

### **Radar Pulsed Power Transistor** 380 WATTS, 1.2-1.4 GHz, 150us Pulse, 10% DUTY

**Production** 02 Feb 2012

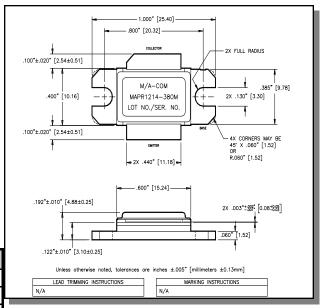
#### **Features**

- **NPN Silicon Microwave Power Transistors**
- Common Base Configuration
- **Broadband Class C Operation**
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metallization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package
- **RoHS Compliant**

#### Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	88	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	Ic	23.9	Α
Power Dissipation @ +25°C	P <sub>TOT</sub>	700	W
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

#### **Outline Drawing**



Electrical Specifications:  $T_c = 25 \pm 5$ °C (ROOM AMBIENT)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA		$BV_CES$	90	-	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 44V		I <sub>CES</sub>	-	10	mA
Thermal Resistance	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	R <sub>TH(JC)</sub>	-	0.25	°C/W
Output Power	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	Po	380	-	W
Power Gain	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	$G_P$	8.8	-	dB
Gain Flatness	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	ΔG <sub>P</sub>		1	dB
Droop	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	Droop	-	0.6	dB
Collector Efficiency	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	ης	45	-	%
Input Return Loss	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	RL	-	-9	dB
Load Mismatch Tolerance	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	2:1	-
Load Mismatch Stability	Vcc = 44V, Pin = 50W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

<sup>•</sup> China Tel: +86.21.2407.1588



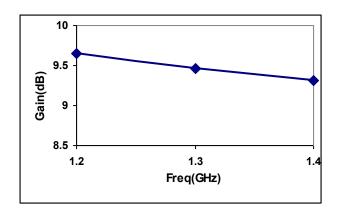
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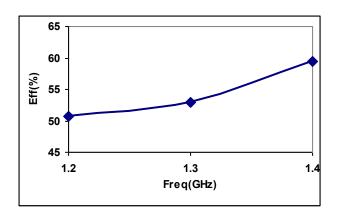
#### **Typical RF Performance**

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	ΔGain (dB)	Eff (%)	RL (dB)	Droop (dB)	VSWR-S 1.5:1	VSWR-T 2:01
1.2	50	458.5	9.65		50.75	-23.6	0.15	S	Р
1.3	50	436.8	9.46		52.88	-16.8	-0.02	S	Р
1.4	50	421.3	9.31	0.34	59.52	-15.2	-0.01	S	Р

### Gain vs. Frequency



### Collector Efficiency vs. Frequency



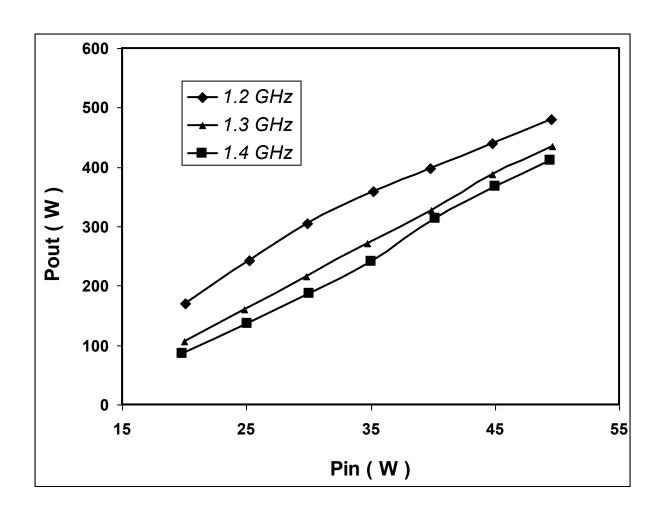
<sup>•</sup> India Tel: +91.80.43537383



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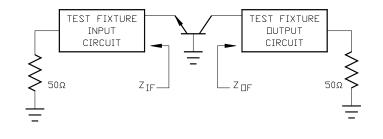
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**RF Power Transfer Curve** (Output Power Vs. Input Power)



### **Broadband Test Fixture Impedance**

F (MHz)	<b>Z</b> <sub>IF</sub> (Ω)	<b>Z</b> <sub>OF</sub> (Ω)
1200	1.3 - j1.89	1.08 - j1.83
1300	1.43 - j1.28	1.08 - j1.24
1400	1.51 - j0.73	1.1 - j0.75



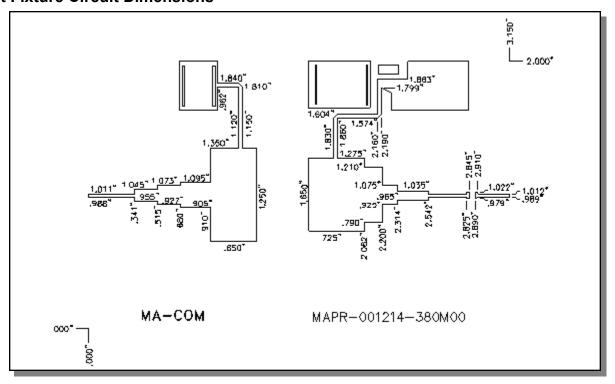
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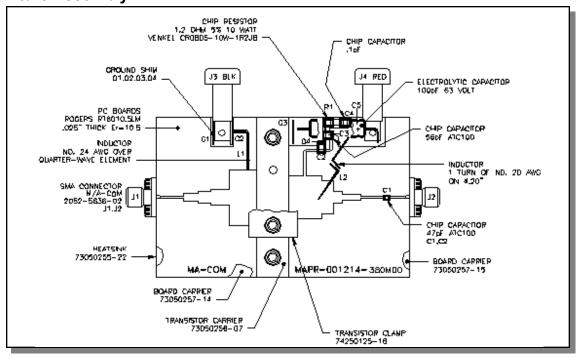
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#### **Test Fixture Circuit Dimensions**



#### **Test Fixture Assembly**



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